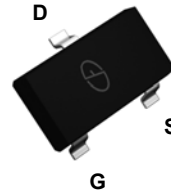
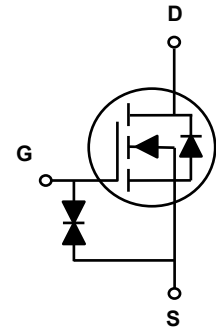


Main Product Characteristics

BV_{DSS}	20V
$R_{DS(ON)}$	300m Ω
I_D	800mA



SOT-323



Schematic Diagram



Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

Description

The GSFC10200 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Drain Current-Continuous ($T_A=25^\circ\text{C}$)	I_D	800	mA
Drain Current-Continuous ($T_A=70^\circ\text{C}$)		640	
Drain Current-Pulsed ¹	I_{DM}	3.2	A
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	275	W
Power Dissipation-Derate above 25 $^\circ\text{C}$		2.2	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	450	$^\circ\text{C}/\text{W}$
Operating Junction Temperature Range	T_J	-55 To +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 To +150	$^\circ\text{C}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On/Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=1\text{mA}$	-	-0.01	-	$V/^{\circ}\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V,$ $T_J=25^{\circ}\text{C}$	-	-	1	μA
		$V_{DS}=16V, V_{GS}=0V,$ $T_J=125^{\circ}\text{C}$	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$	-	-	± 10	μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=0.5A$	-	200	300	m Ω
		$V_{GS}=2.5V, I_D=0.4A$	-	235	400	
		$V_{GS}=1.8V, I_D=0.2A$	-	295	550	
		$V_{GS}=1.5V, I_D=0.1A$	-	365	800	
		$V_{GS}=1.2V, I_D=0.1A$	-	600	1500	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.3	0.6	1.0	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		-	3	-	mV/ $^{\circ}\text{C}$
Dynamic and Switching Characteristics						
Total Gate Charge ^{2,3}	Q_g	$V_{DS}=10V, I_D=0.5A,$ $V_{GS}=4.5V$	-	1	2	nC
Gate-Source Charge ^{2,3}	Q_{gs}		-	0.26	0.5	
Gate-Drain Charge ^{2,3}	Q_{gd}		-	0.2	0.4	
Turn-On Delay Time ^{2,3}	$t_{d(on)}$	$V_{DD}=10V, R_G=10\Omega,$ $V_{GS}=4.5V, I_D=0.5A$	-	5	10	nS
Rise Time ^{2,3}	t_r		-	3.5	7	
Turn-Off Delay Time ^{2,3}	$t_{d(off)}$		-	14	28	
Fall Time ^{2,3}	t_f		-	6	12	
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1\text{MHz}$	-	38.2	75	pF
Output Capacitance	C_{oss}		-	14.4	28	
Reverse Transfer Capacitance	C_{rss}		-	6	12	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V,$ Force Current	-	-	0.8	A
Pulsed Source Current	I_{SM}		-	-	1.6	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=0.5A,$ $T_J=25^{\circ}\text{C}$	-	-	1	V

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operation temperature.

Typical Electrical and Thermal Characteristic Curves

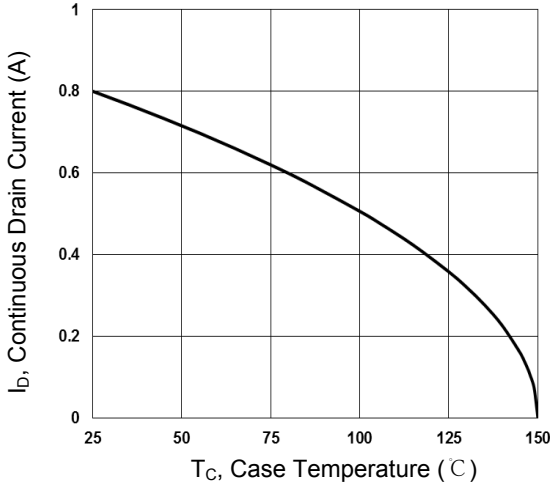


Figure 1. Continuous Drain Current vs. T_c

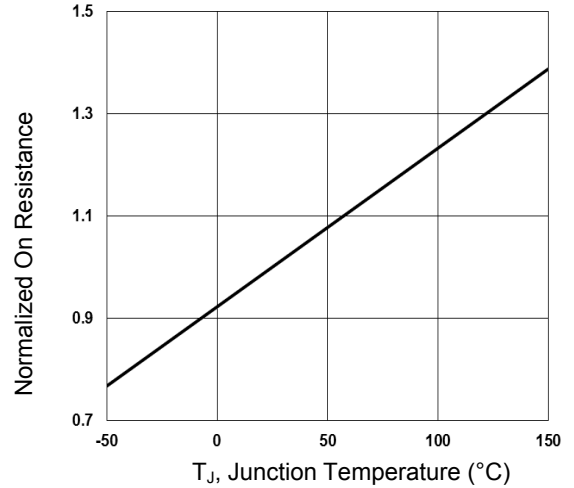


Figure 2. Normalized R_{DSON} vs. T_j

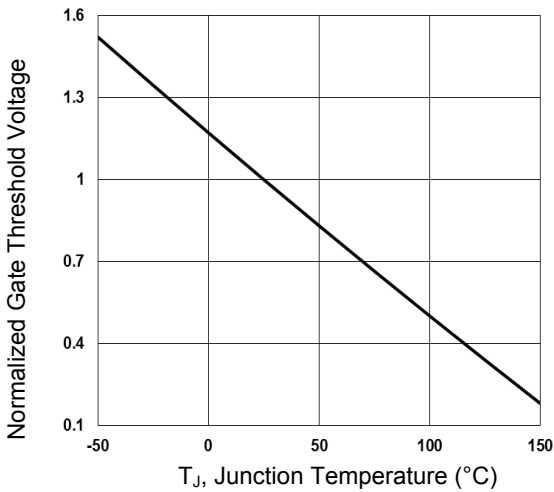


Figure 3. Normalized V_{th} vs. T_j

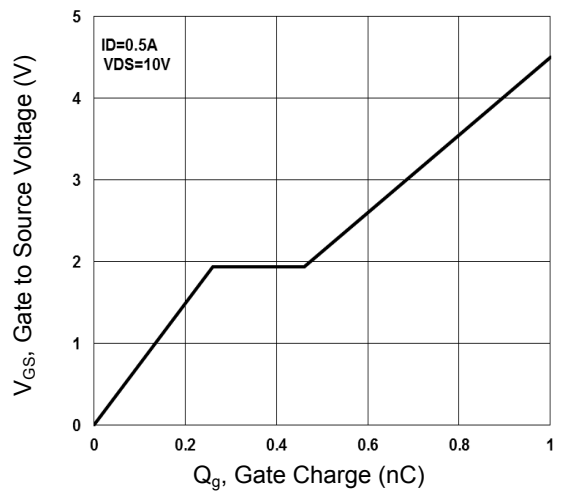


Figure 4. Gate Charge Waveform

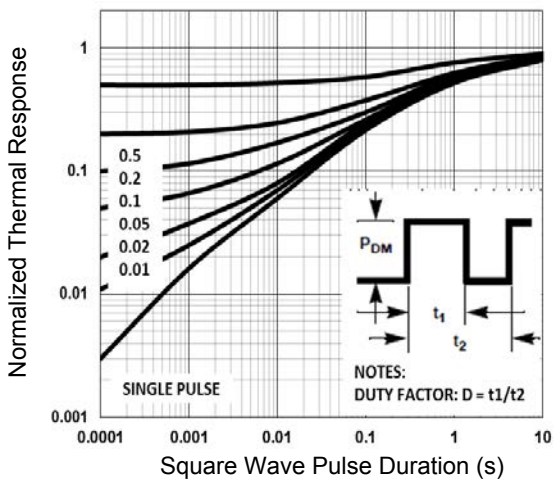


Figure 5. Normalized Transient Response

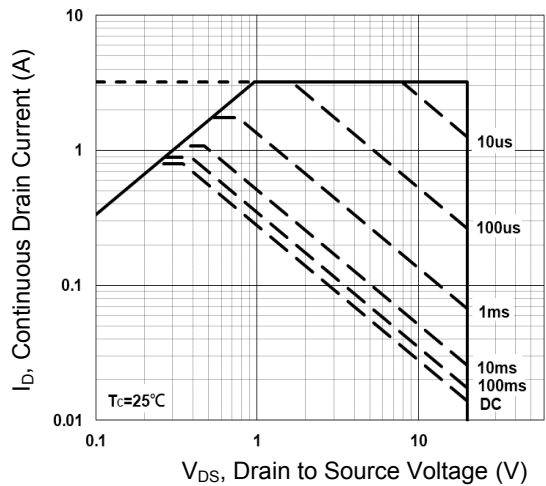


Figure 6. Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

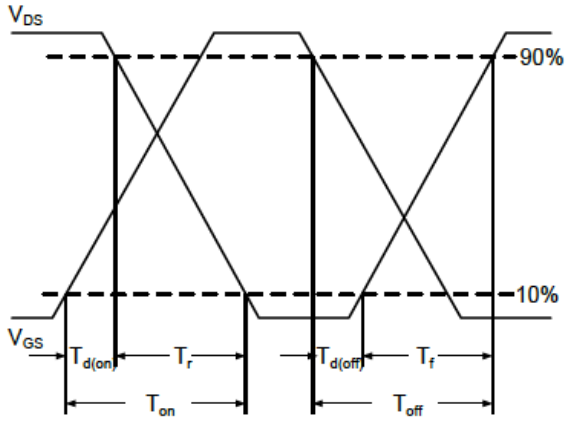


Figure 7. Switching Time Waveform

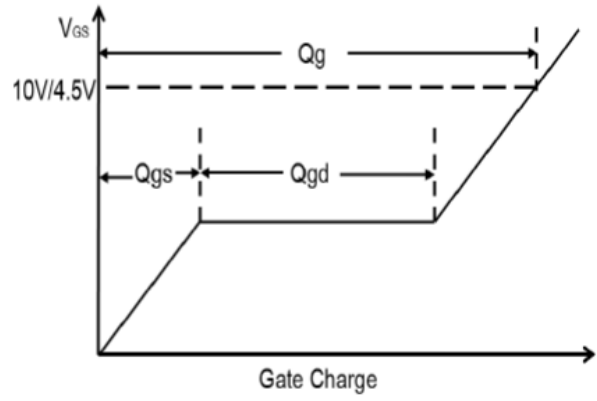
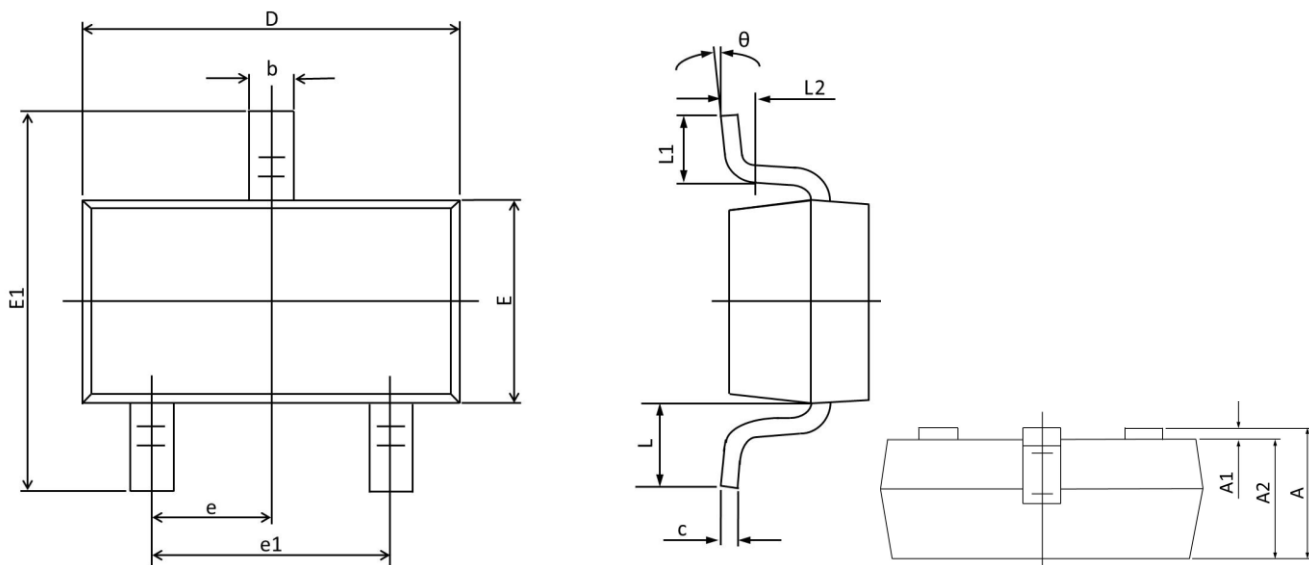


Figure 8. Gate Charge Waveform

Package Outline Dimensions (SOT-323)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
A1	0.100	0.000	0.004	0.000
A2	1.000	0.800	0.039	0.031
b	0.400	0.200	0.016	0.008
c	0.250	0.080	0.010	0.003
D	2.200	1.800	0.087	0.071
E	1.350	1.150	0.053	0.045
E1	2.450	1.800	0.096	0.071
e	0.65BSC		0.026BSC	
e1	1.400	1.200	0.055	0.047
L	0.525REF.		0.021REF.	
L1	0.460	0.150	0.018	0.006
L2	0.200	0.000	0.008	0.000
θ	8°	0°	8°	0°